

Device Modeling Report

COMPONENTS: Silicon Carbide Schottky Diode
PART NUMBER: STPSC806
MANUFACTURER: STMicroelectronics
REMARK: Professional Model

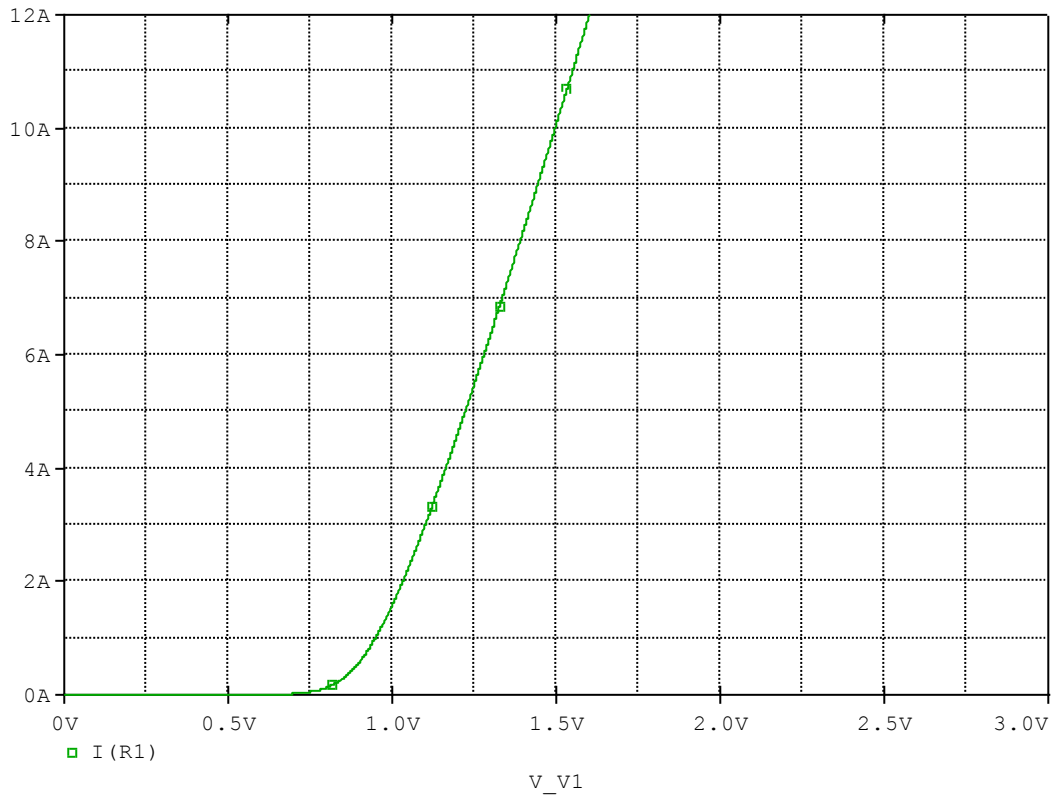


Bee Technologies Inc.

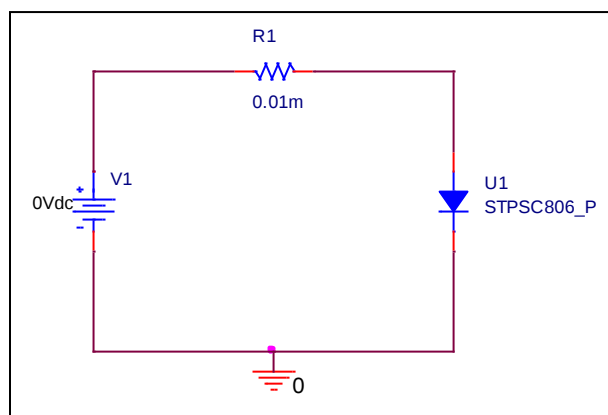
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

Forward Current Characteristic

Circuit Simulation Result

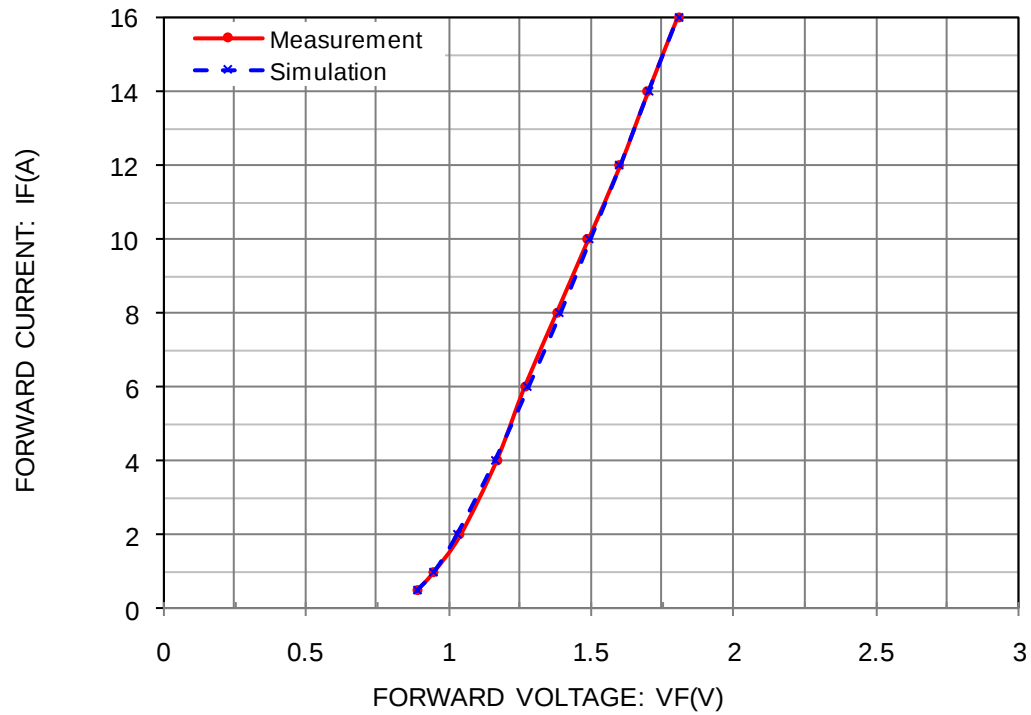


Evaluation Circuit



Comparison Graph

Circuit Simulation Result



Simulation Result

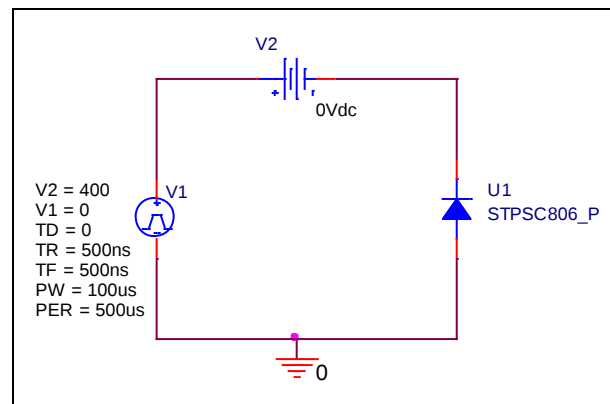
I_F (A)	V_F (V)		Error (%)
	Measurement	Simulation	
0.5	0.8900	0.8888	-0.14
1	0.9500	0.9485	-0.16
2	1.0400	1.0320	-0.77
4	1.1700	1.1632	-0.58
6	1.2700	1.2795	0.75
8	1.3800	1.3897	0.70
10	1.4900	1.4965	0.44
12	1.6000	1.6013	0.08
14	1.7000	1.7046	0.27
16	1.8100	1.8068	-0.18

Junction Capacitance Characteristic

Circuit Simulation Result

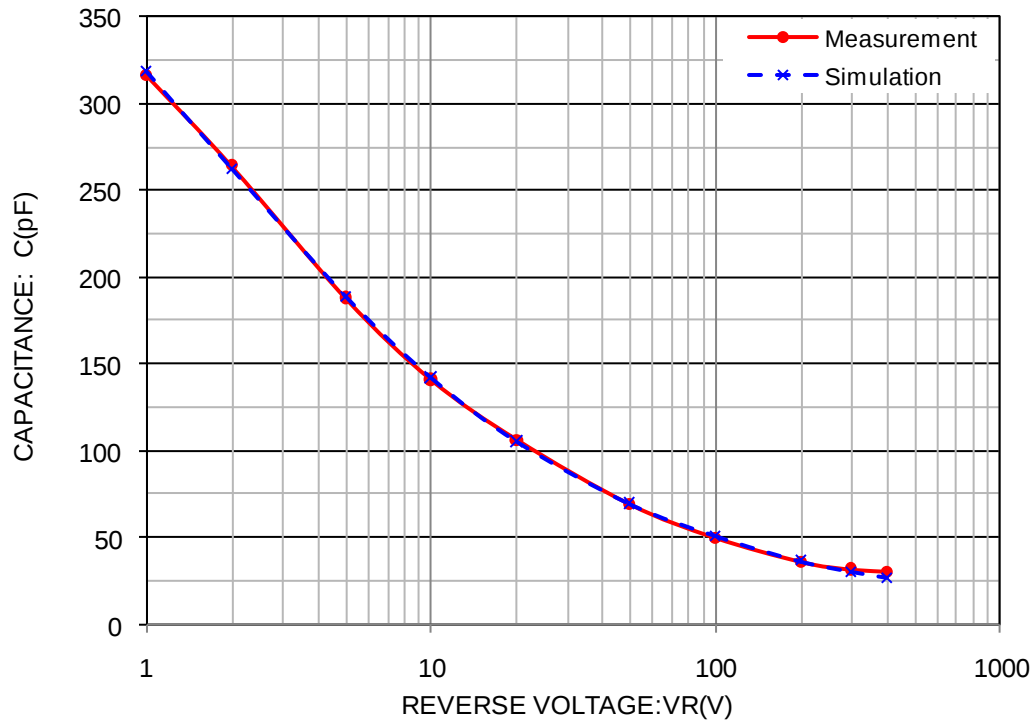


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

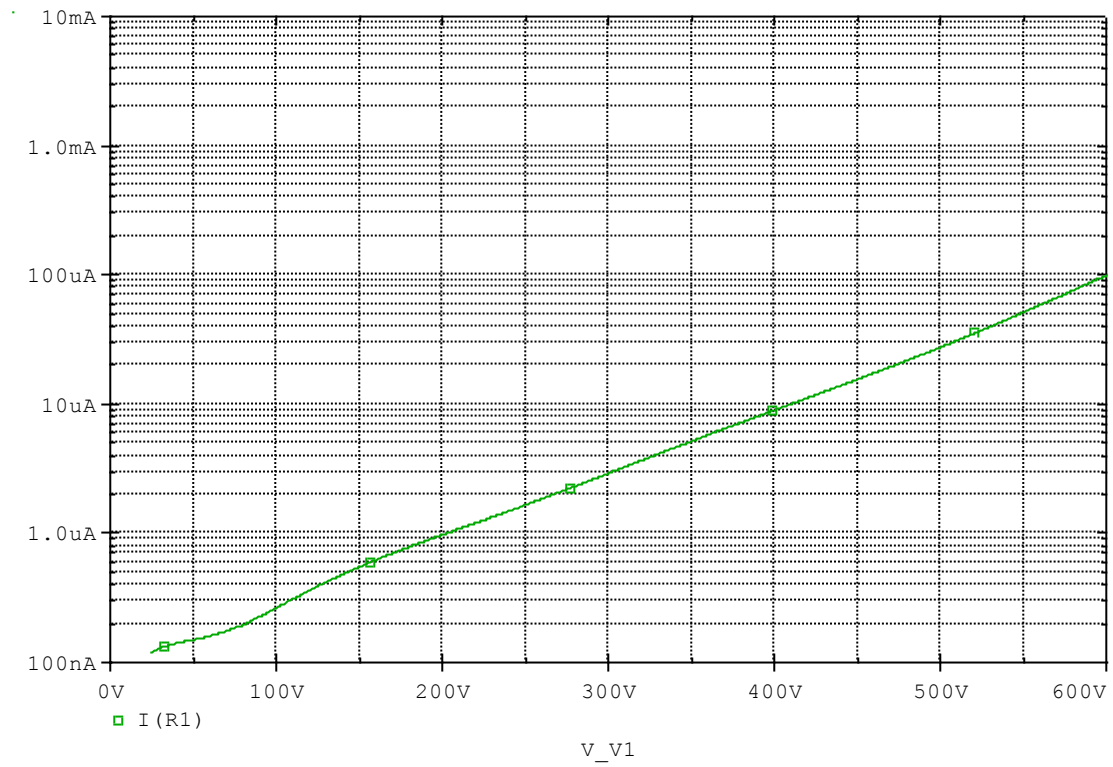


Simulation Result

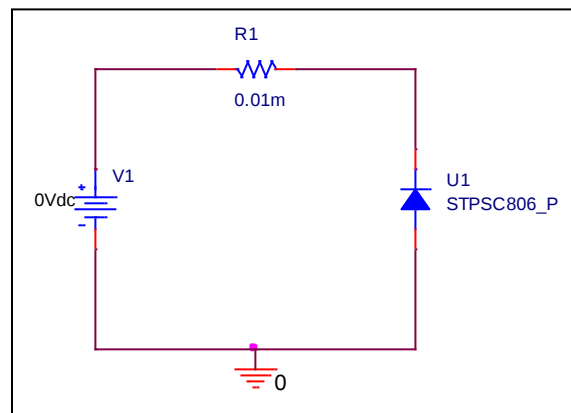
V_R (V)	C (pF)		Error (%)
	Measurement	Simulation	
1	316.000	318.455	0.78
2	264.000	261.941	-0.78
5	188.000	188.931	0.50
10	141.000	142.230	0.87
20	106.000	105.249	-0.71
50	69.000	69.621	0.90
100	50.000	50.668	1.34
200	36.000	36.762	2.12
300	32.000	30.483	-4.74

Reverse Characteristic

Circuit Simulation Result

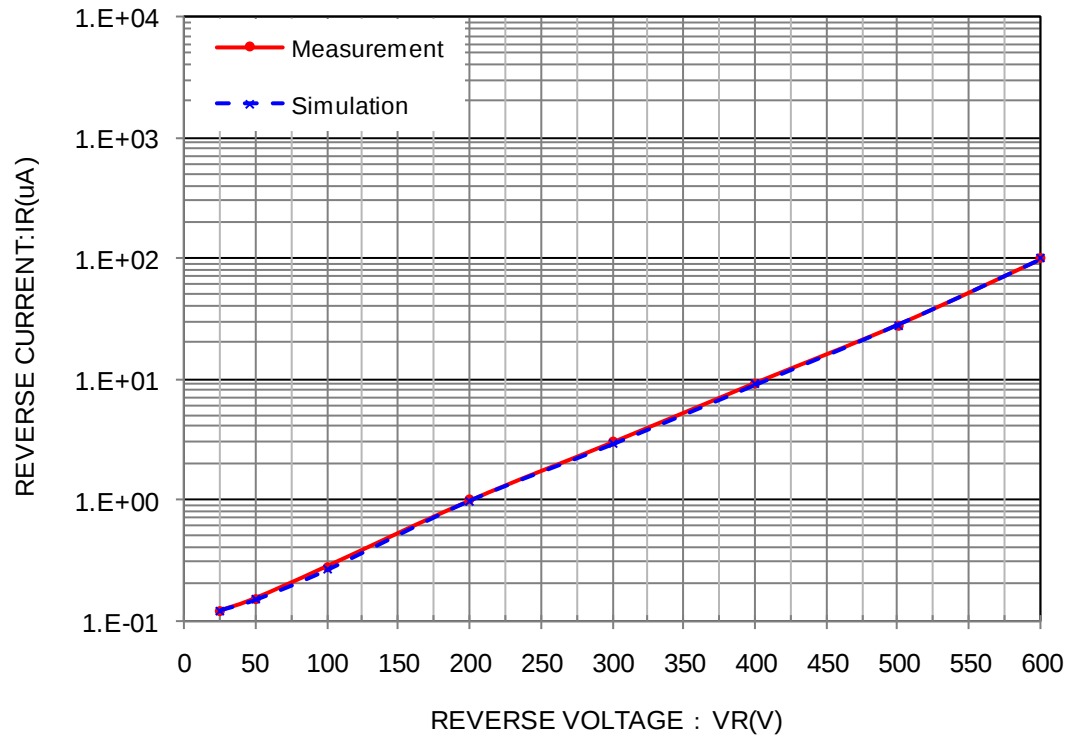


Evaluation Circuit



Comparison Graph

Circuit Simulation Result



Simulation Result

$V_R(V)$	$I_R(\mu A)$		Error (%)
	Measurement	Simulation	
25	0.120	0.120	-0.23
50	0.150	0.149	-0.52
100	0.275	0.264	-3.88
200	1.000	0.972	-2.80
300	3.000	2.910	-2.99
400	9.200	8.987	-2.32
500	28.000	27.569	-1.54
600	100.000	99.226	-0.77